CST60P02D P-Ch 20V Fast Switching MOSFETs

★ Super Low Gate Charge
★ Green Device Available
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

CST60P02D Product Summary

Green

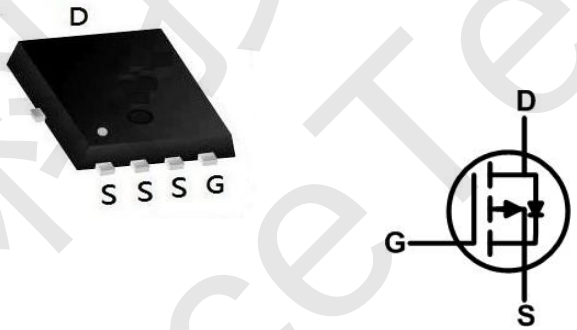
BVDSS	RDSON	ID
-20V	6mΩ	-60A

CST60P02D Description

The CST60P02D is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The CST60P02D meet the RoHS and Green Product requirement with full function reliability approved.

CST60P02D PDFN3333-8L Pin Configuration



CST60P02D Absolute Maximum Ratings (T_A = 25°C, unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±10	V
Continuous Drain Current	T_C=25°C	I_D	-60	A
	T_C=100°C		-34.8	
Pulsed Drain Current[1]		I_{DM}	-220	A
Single Pulse Avalanche Energy[2]		EAS	61.25	mJ
Total Power Dissipation	T_C=25°C	P_D	39	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

CST60P02D Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient[3]	$R_{\theta JA}$	38	°C/W
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	3.2	°C/W

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CST60P02D Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-20	-	-	V
Gate-body Leakage current		I_{GSS}	V_{DS} = 0V, V_{GS} = ±10V	-	-	±100	nA
Zero Gate Voltage Drain Current	T_J=25°C	I_{DSS}	V_{DS} = -20V, V_{GS} = 0V	-	-	-1	μA
	T_J=100°C			-	-	-100	
Gate-Threshold Voltage		$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-0.4	-	-1.0	V
Drain-Source on-Resistance[4]		$R_{DS(on)}$	V_{GS} = -4.5V, I_D = -15A	-	6	8.2	mΩ
			V_{GS} = -2.5V, I_D = -10A	-	7.5	10	
			V_{GS} = -1.8V, I_D = -8A	-	10.2	15	
Forward Transconductance[4]		g_{fs}	V_{DS}= -5V, I_D= -15A	-	78	-	S
Dynamic Characteristics[5]							
Input Capacitance		C_{iss}	V_{DS} = -10V, V_{GS} =0V, f =1MHz	-	3560	-	pF
Output Capacitance		C_{oss}		-	500	-	
Reverse Transfer Capacitance		C_{rss}		-	430	-	
Gate Resistance		R_g	f = 1MHz	-	11	-	Ω
Switching Characteristics[5]							
Total Gate Charge		Q_g	V_{GS} = -4.5V, V_{DS} = -10V, I_D= -15A	-	43	-	nC
Gate-Source Charge		Q_{gs}		-	7.9	-	
Gate-Drain Charge		Q_{gd}		-	11.2	-	
Turn-on Delay Time		$t_{d(on)}$	V_{GS} = -4.5V, V_{DD} = -10V, R_G = 3Ω, I_D= -15A,	-	14.5	-	ns
Rise Time		t_r		-	20.2	-	
Turn-off Delay Time		$t_{d(off)}$		-	93	-	
Fall Time		t_f		-	161	-	
Body Diode Reverse Recovery Time		t_{rr}	I_F = -15A, dI_F/dt = 100A/μs	-	28	-	ns
Body Diode Reverse Recovery Charge		Q_{rr}		-	25.7	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage[4]		V_{SD}	I_S = -1A, V_{GS} = 0V	-	-	-1.2	V
Continuous Source Current	T_C=25°C	I_S	-	-	-	-60	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
2. The EAS data shows Max. rating . The test condition is V_{DD}= -25V, V_{GS}= -10V, L= 0.1mH, I_{AS}= 35A.
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

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CST60P02D Typical Characteristics

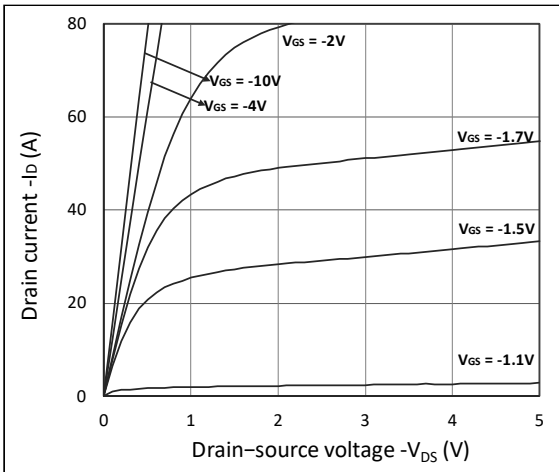


Figure 1. Output Characteristics

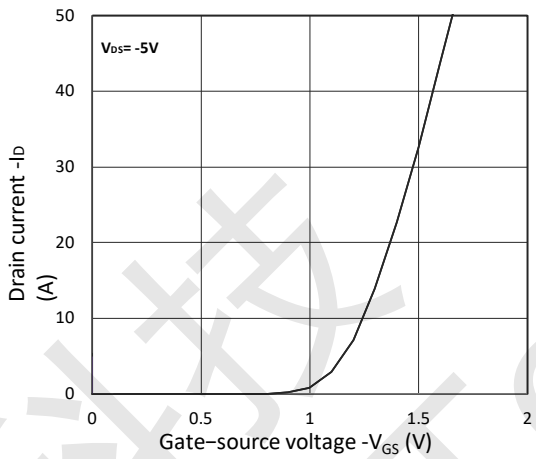


Figure 2. Transfer Characteristics

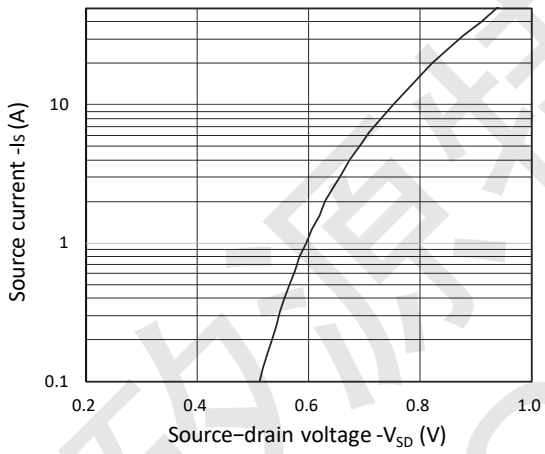


Figure 3. Forward Characteristics of Reverse

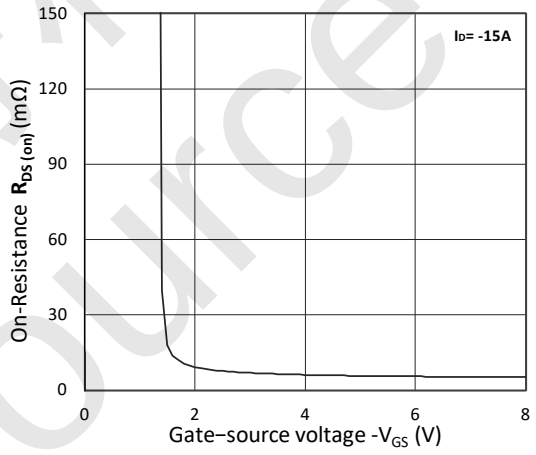


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

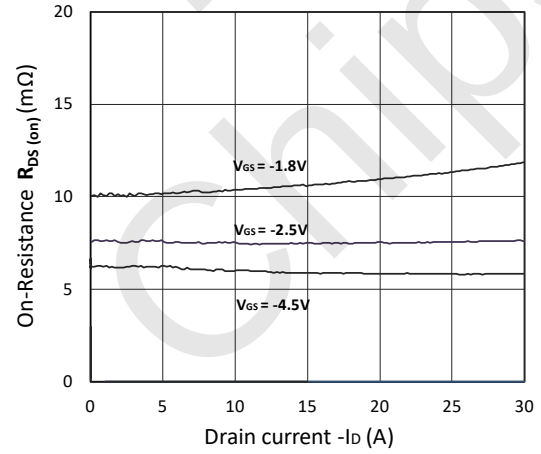


Figure 5. $R_{DS(ON)}$ vs. I_D

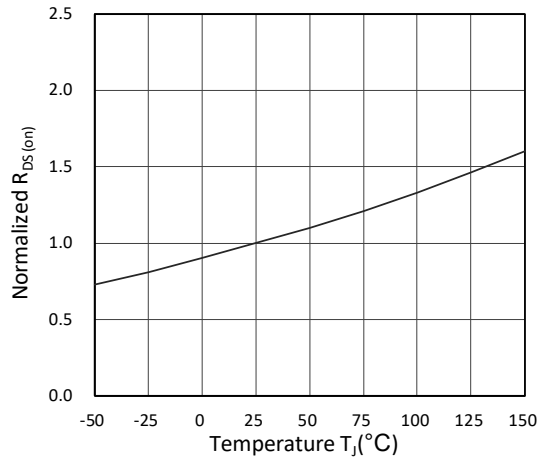


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

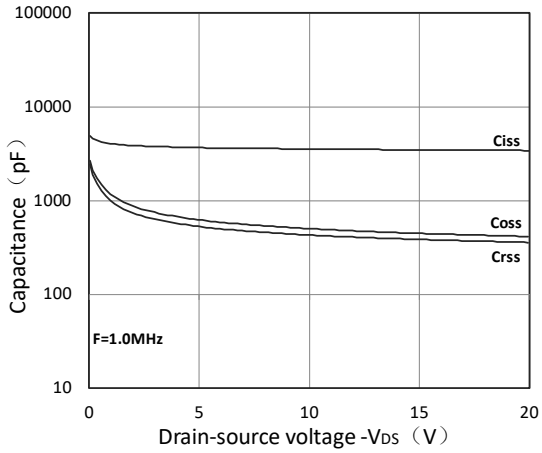


Figure 7. Capacitance Characteristics

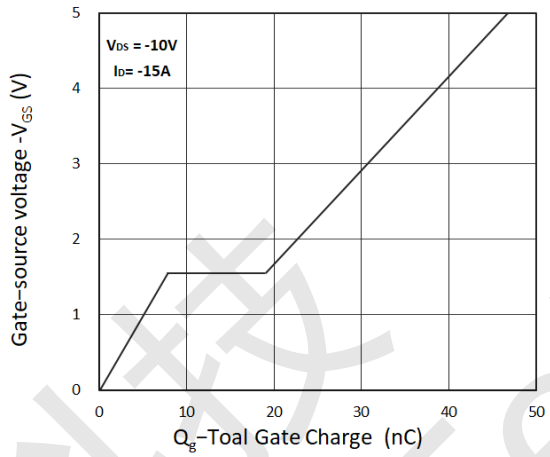


Figure 8. Gate Charge Characteristics

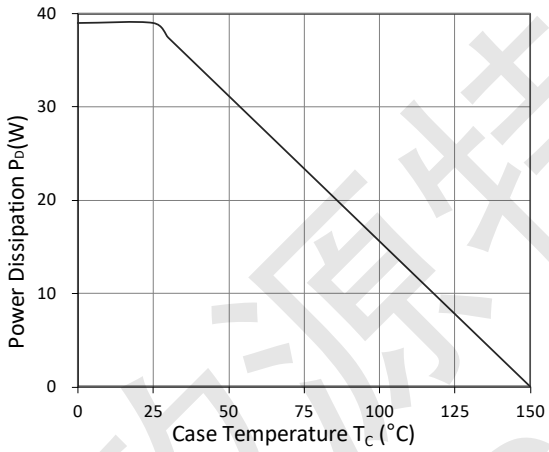


Figure 9. Power Dissipation

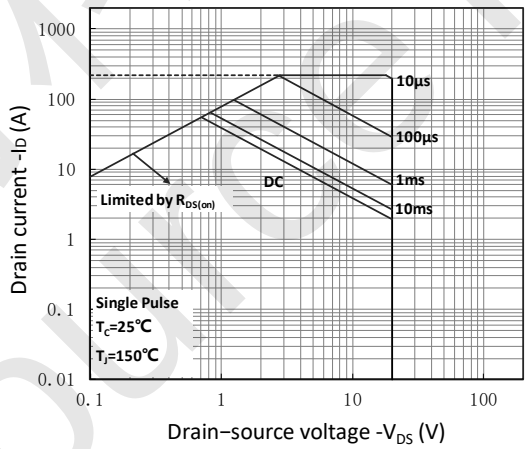


Figure10. Safe Operating Area

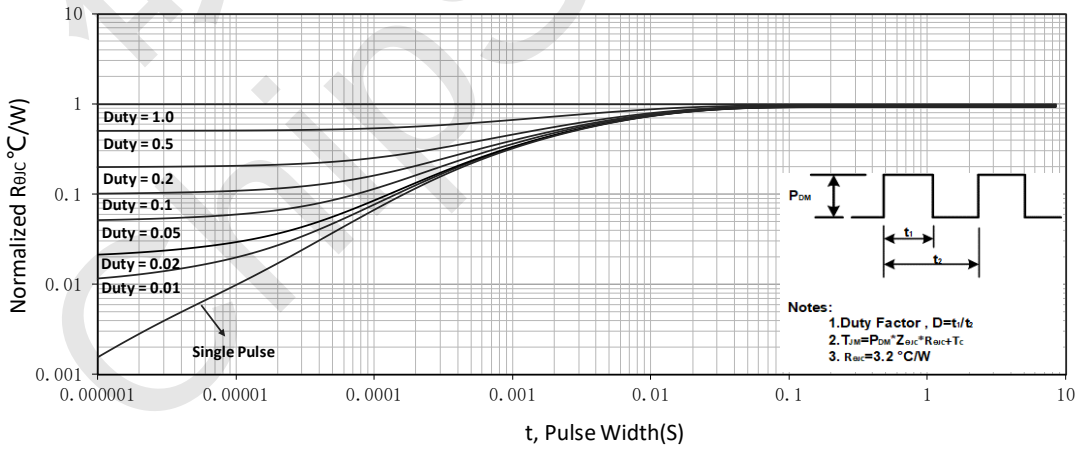


Figure 11. Normalized Maximum Transient Thermal Impedance

CST60P02D Test Circuit

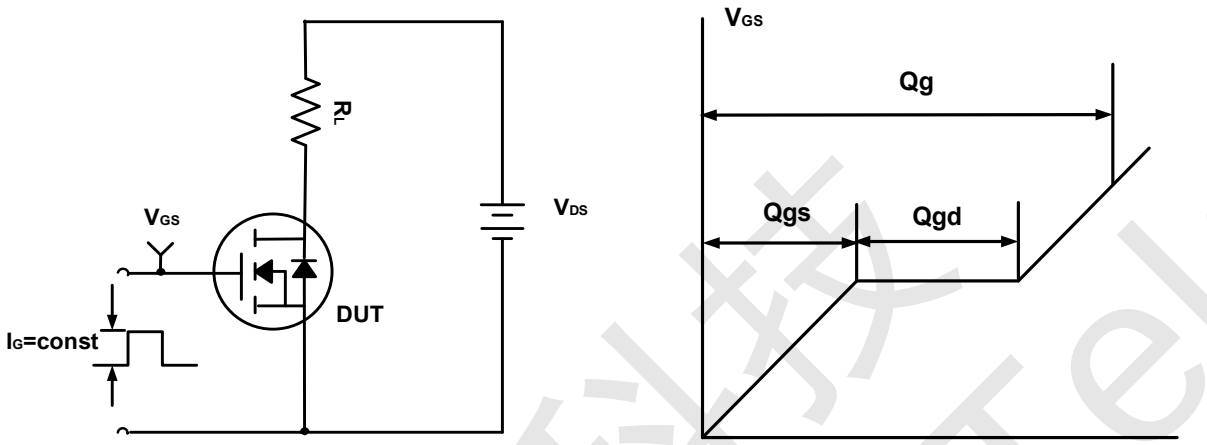


Figure A. Gate Charge Test Circuit & Waveforms

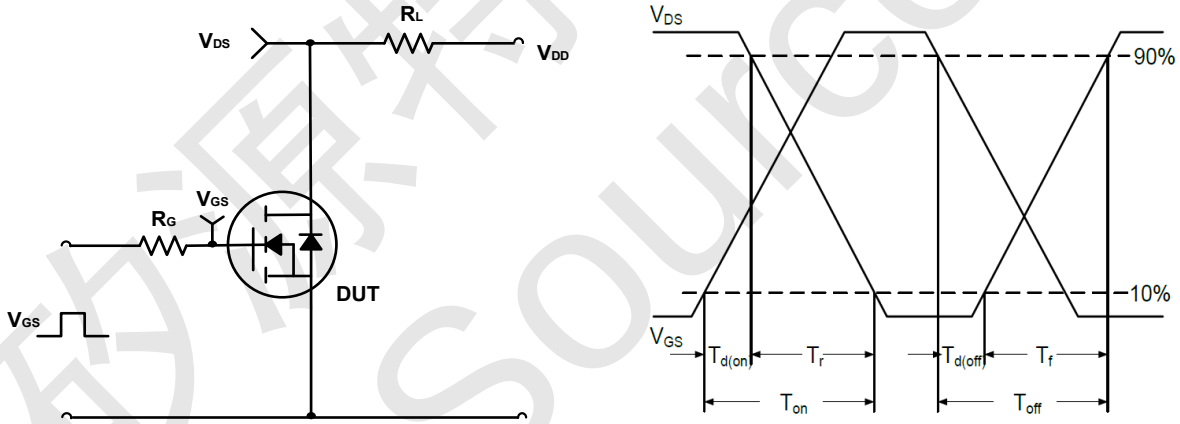


Figure B. Switching Test Circuit & Waveforms

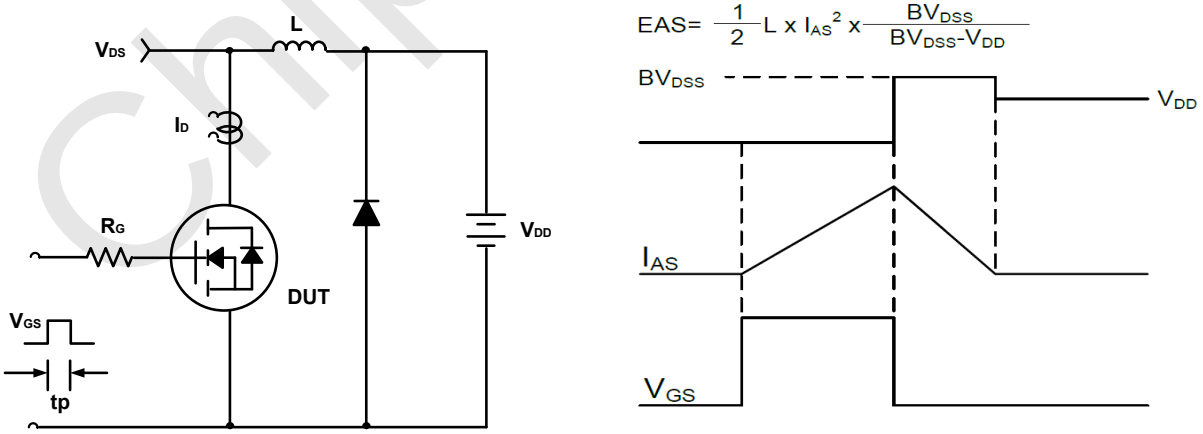
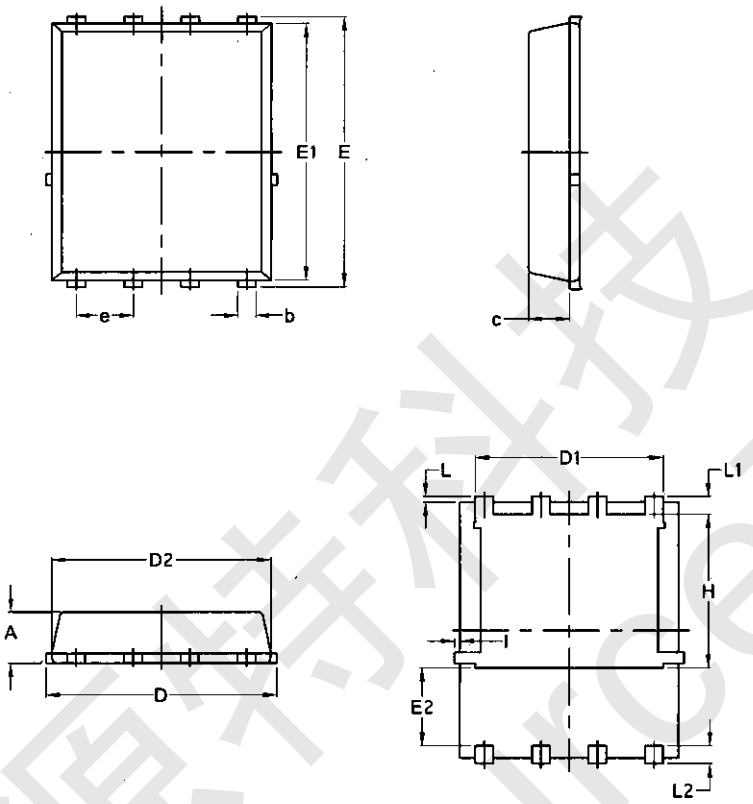


Figure C. Unclamped Inductive Switching Circuit & Waveforms

CST60P02D Package Mechanical Data-PDFN3333-8L-Single



COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.80	0.90
A1	0.00	0.03	0.05
b	0.24	0.30	0.35
c	0.10	0.15	0.20
D	3.25	3.32	3.40
D1	3.05	3.15	3.25
D2	2.40	2.50	2.60
E	3.00	3.10	3.20
E1	1.35	1.45	1.55
e	0.65 BSC.		
H	3.20	3.30	3.40
L	0.30	0.40	0.50
L1	0.10	0.15	0.20
L2	1.13 REF.		